

技术数据表

特点 (C) :

- * High reliability High radiant intensity Low forward voltage
- * Fast response time High photo sensitivity
- * 940nm
- Cut-off visible wavelength λp=940nm
- * Rohs
- Pb.Free RoHS compliant version
- * MSL :2
- Moisture sensitivity level MSL :2 levels



应用领域 (P) :

- * Slot machines
- * Small home appliances
- * Automatic Sensors
- * Fax machine
- * Scanner



目录

Catalo

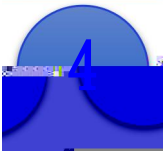
电性参数

◆极限参数 =25 : Absolute Maximum Ratings (Temperature=25℃):

Input Emitter	Power Dissipation*1	PD	75	mW
	Continuous Forward Current	IF	50	mA
	Peak Forward Current*2	IF	1	A
	Reverse Voltage	VR	5	V
Output Detector	Power Dissipation*1	PD	75	mW
	- Collector-Emitter Voltage	VCEO	30	V
	- Emitter-Collector Voltage	VECO	5	V
	Collector Current	IC(on)	20	mA
Operating Temperature		Topr	-20~+85	
Storage Temperature		Tstg	-40~+85	
Lead Soldering Temperature*3		Tsol	260	



光電特性 (溫度=25℃) :
Electro-Optical Characteristics (



电压公差

:

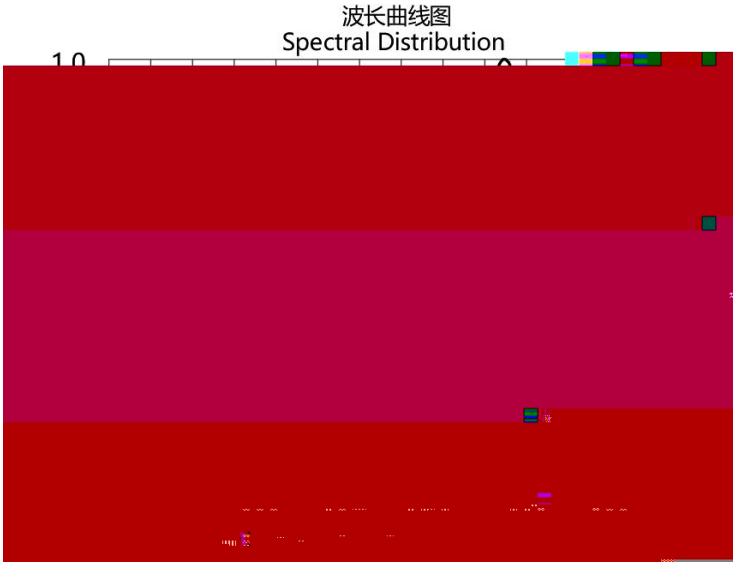
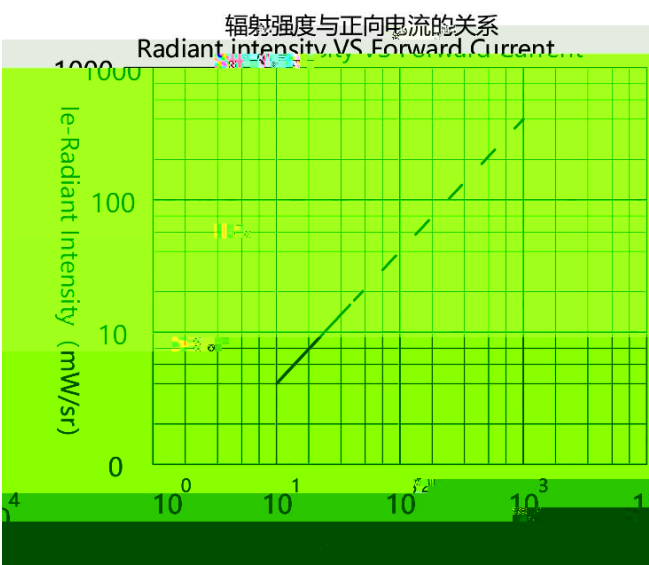
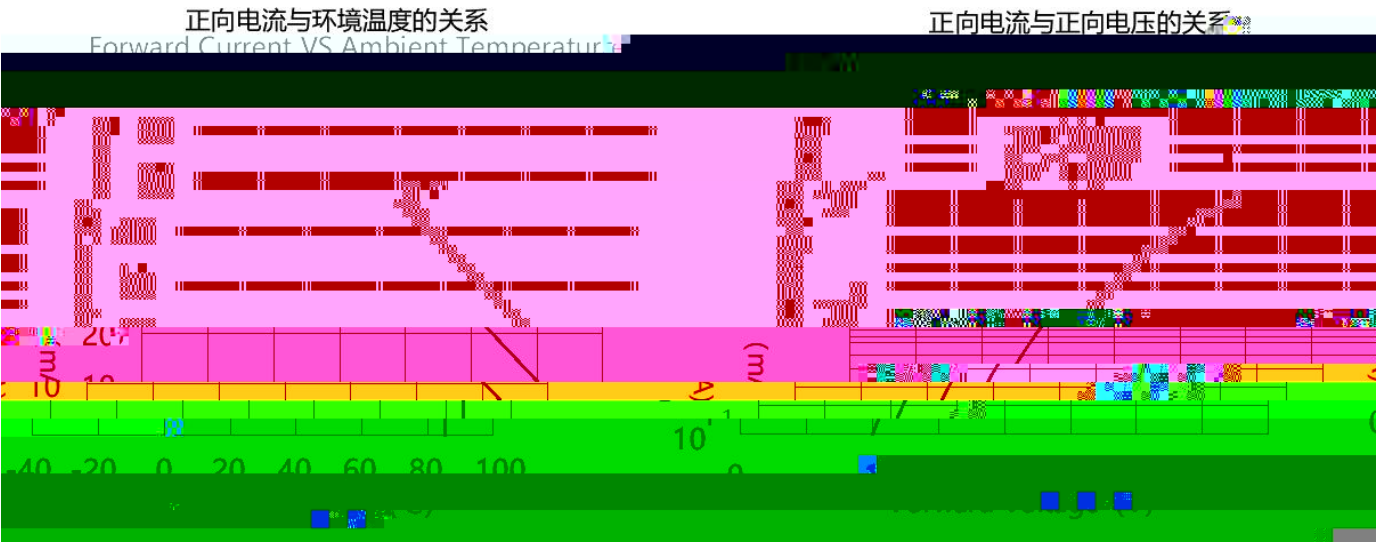
代码	最小值	最大值	单位	测试条件
R2-4	1.2	1.6	V	IF=20mA

光电流公差:
Collector Current grading:

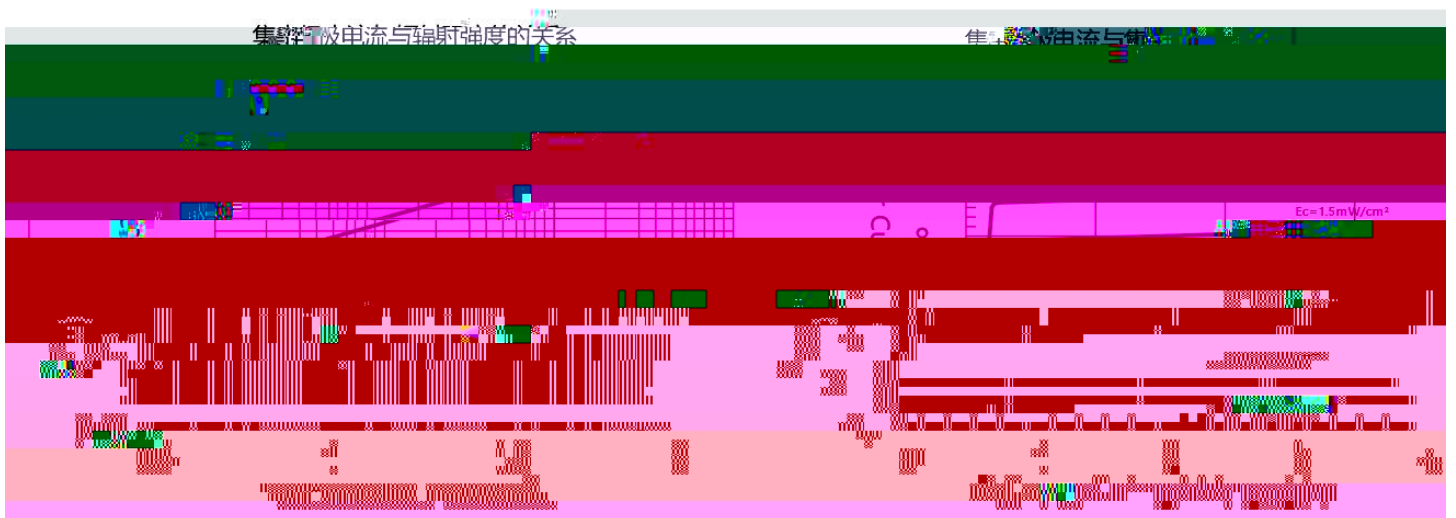
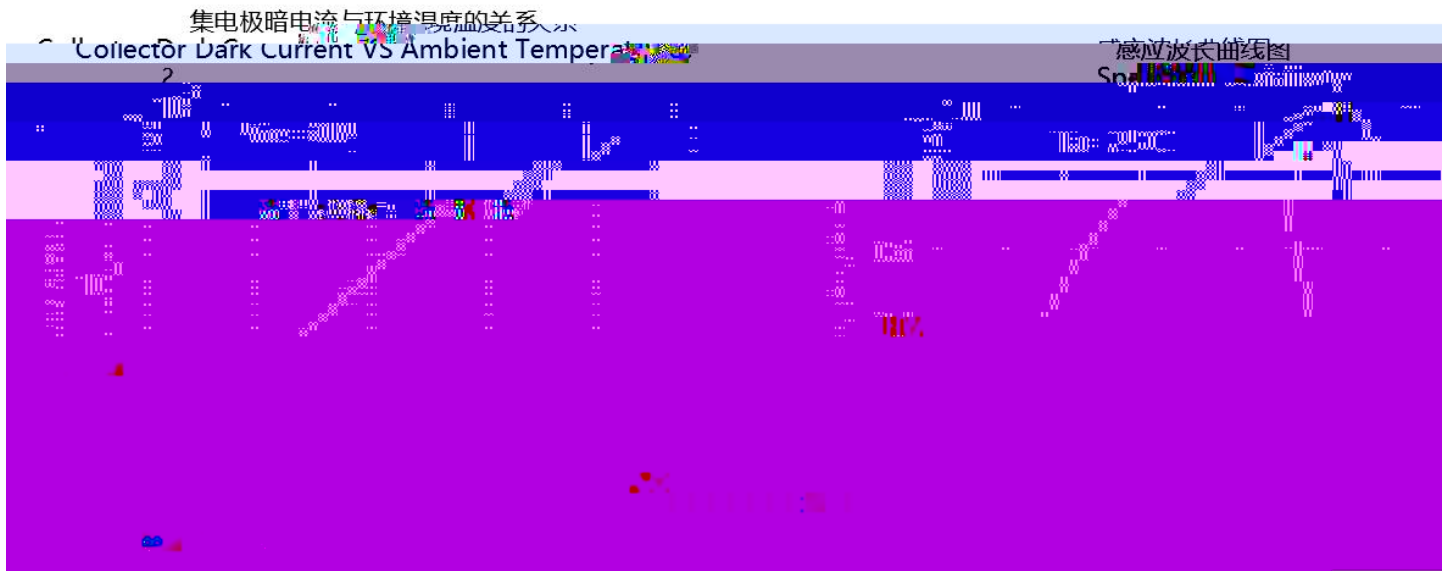
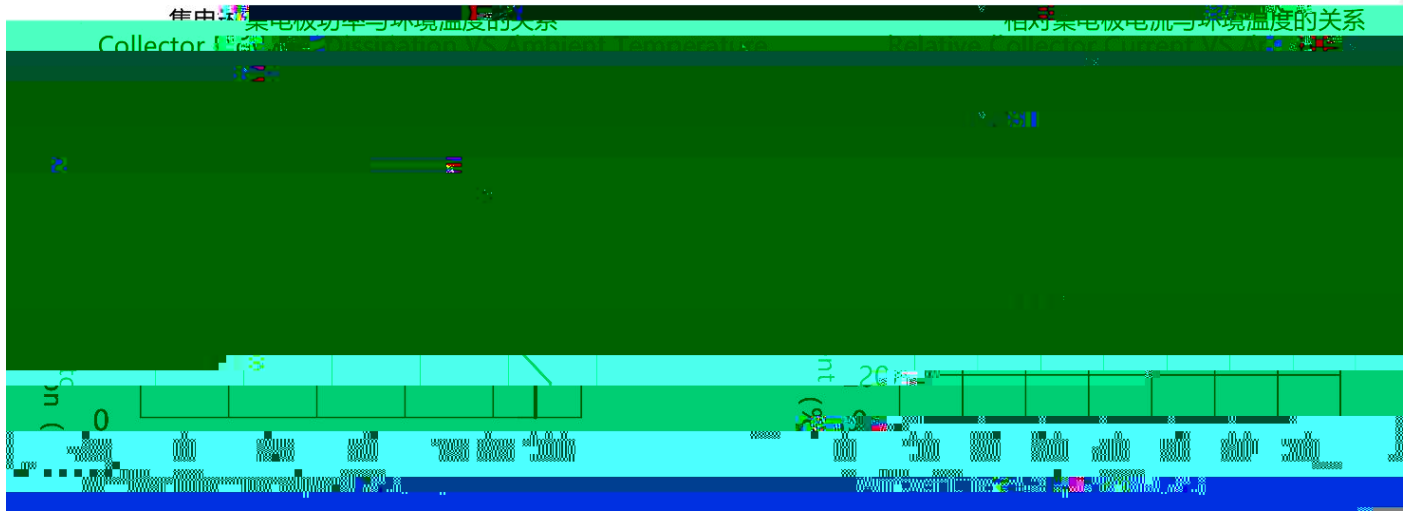
代码	最小值	最大值	单位	测试条件
IC27-39	8	20	mA	IF=20mA VCE=5V

典型特性曲线

发射管特性曲线图 Typical Electro-Optical Characteristics Curves-IR



接收管特性曲线图 Typical Electro-Optical Characteristics Curves-PT



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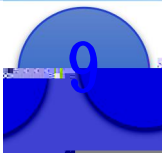
外形尺寸

1. mm

Remarks: 1 Unit: mm

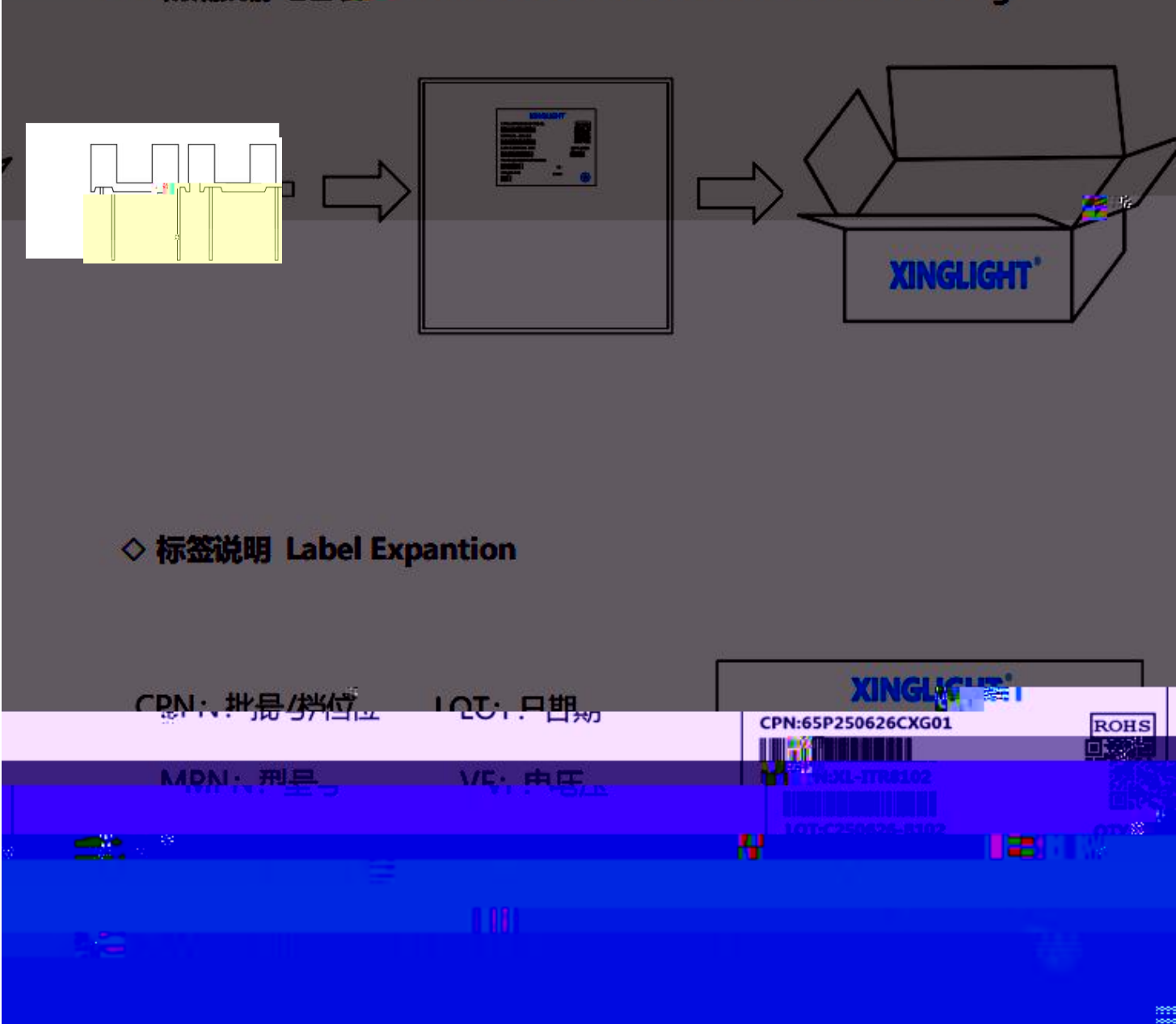
2. 0.3mm

2. Tolerance: 0.3mm mn ,



包装

◇ 防潮抗静电包装 Moisture Proof and Antti-Electrostatic Foil Bag



◇ 标签说明 Label Expantion

CPN: 批号/档位 LOT: 日期

MDN: 型号 VF: 电压

CPN:65P250626CXG01

ROHS

XGL-17R8102

LOT:65P250626CXG01

QTY

DATE

TIME

USER

REMARK

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使用注意事項

NPN

IR

IR PT

This product It is composed of infrared emission diode and NPN silicon photo transistor, which are packaged side by side in black On the converging optical axis in the thermoplastic shell. Photo transistor only receives radiation from IR. This is normal Condition. But when the object is in the middle, the photo transistor cannot receive radiation. For more component information, please Refer to IR and PT.

If there are any modifications to the specification sheet, no further notice will be given

